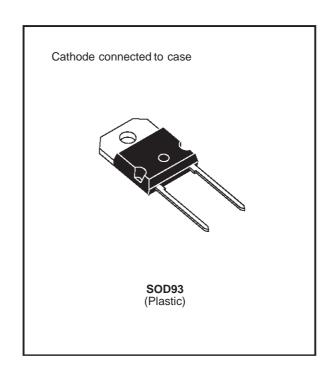


FAST RECOVERY RECTIFIER DIODE

- VERY HIGH REVERSE VOLTAGE CAPABILITY
- VERY LOW REVERSE RECOVERY TIME
- VERY LOW SWITCHING LOSSES
- LOW NOISE TURN-OFF SWITCHING



SUITABLE APPLICATIONS

- FREE WHEELING DIODE IN CONVERTERS AND MOTOR CONTROL CIRCUITS
- RECTIFIER IN S.M.P.S.

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit	
V_{RRM}	Repetitive Peak Reverse Voltage	1000	V	
V _{RSM}	Non Repetitive Peak Reverse Voltage	1000	V	
I _{FRM}	Repetive Peak Forward Current	t _p ≤ 10μs	375	А
I _{F (RMS)}	RMS Forward Current	70	А	
I _{F (AV)}	Average Forward Current	$T_c = 85^{\circ}C$ $\delta = 0.5$	30	А
I _{FSM}	Surge non Repetitive Forward Current $t_p = 10 ms$ Sinusoidal		200	А
Р	Power Dissipation	60	W	
T _{stg} T _j	Storage and Junction Temperature Range	- 40 to +150 - 40 to +150	°C	

THERMAL RESISTANCE

	Symbol	Parameter	Value	Unit
ſ	R _{th (j - c)}	Junction-case	1	°C/W

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ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Synbol	Test Conditions			Тур.	Max.	Unit
I _R	T _j = 25°C	$V_R = V_{RRM}$			100	μΑ
	T _j = 100°C				5	mA
V _F	T _j = 25°C	I _F = 30A			1.9	V
	T _j = 100°C				1.8	

RECOVERY CHARACTERISTICS

Symbol	Test Conditions				Min.	Тур.	Max.	Unit
t _{rr}	T _j = 25°C	I _F = 1A	$di_F/dt = -15A/\mu s$	$V_R = 30V$			165	ns
		I _F = 0.5A	I _R = 1A	$I_{rr} = 0.25A$			70	

TURN-OFF SWITCHING CHARACTERISTICS (Without Series Inductance)

Symbol	Test Conditions			Тур.	Max.	Unit
t _{IRM}	$di_F/dt = -120A/\mu s$ $V_{CC} = 200 \text{ V}$ $I_F = 30A$				200	ns
	$di_F/dt = -240A/\mu s$	$L_p \le 0.05 \mu H$ $T_j = 100^{\circ} C$ See figure 11		120		
I _{RM}	di _F /dt = -120A/μs				19.5	А
	$di_F/dt = -240A/\mu s$			22		

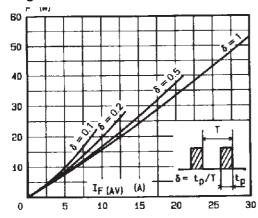
TURN-OFF OVERVOLTAGE COEFFICIENT (With Series Inductance)

Symbol	Test Conditions			Min.	Тур.	Max.	Unit
$C = \frac{V_{RP}}{V_{CC}}$	$T_j = 100^{\circ}C$ $di_F/dt = -30A/\mu s$	$V_{CC} = 200V$ $L_p = 5\mu H$	I _F = I _{F (AV)} See figure 12			4.5	

To evaluate the conduction losses use the following equation:

 $V_F = 1.47 + 0.010 I_F$ $P = 1.47 \times I_{F(AV)} + 0.010 I_F^2(RMS)$

Figure 1. Low frequency power losses versus average current



 $\label{eq:Figure 2. Peak current versus form factor} \textbf{Figure 2. Peak current versus form factor}$

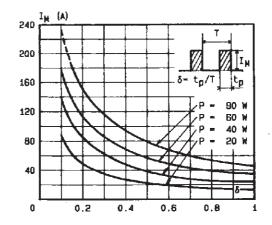


Figure 3. Non repetitive peak surge current versus overload duration

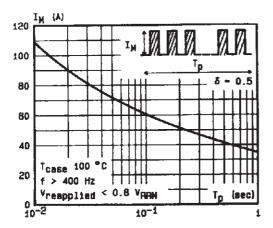


Figure 4. Thermal impedance versus pulse width

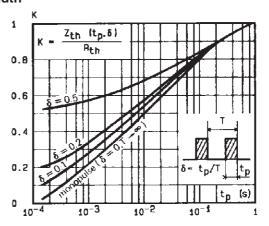


Figure 5. Voltage drop versus forward current

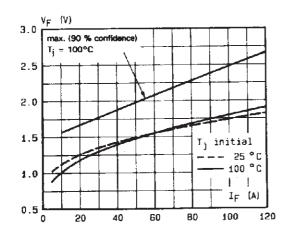


Figure 6. Recovery charge versus di_F/d_t-

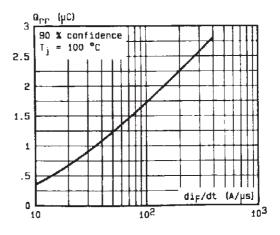


Figure 7. Recovery time versus dif/dt-

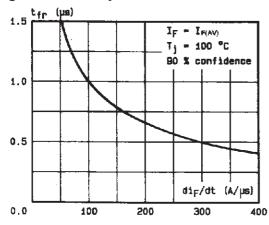
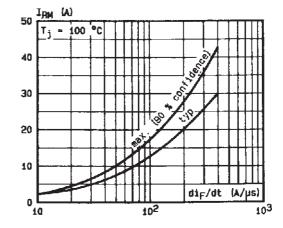


Figure 8. Peak reverse current versus di_F/d_{t-}



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Figure 9. Peak forward voltage versus dif/dt-

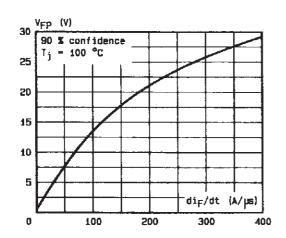


Figure 10. Dynamic parameters versus junction temperature.

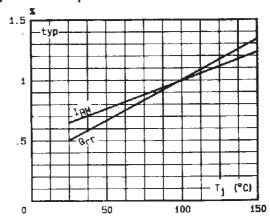


Figure 11. Turn-off switching characteristics (without series inductance).

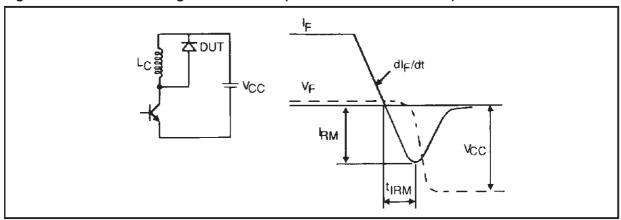
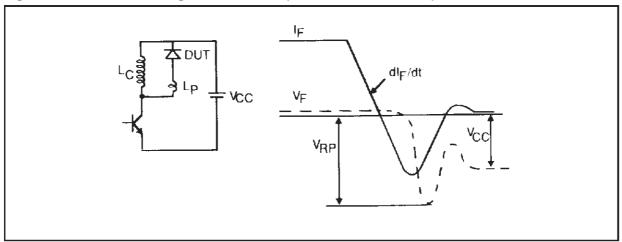


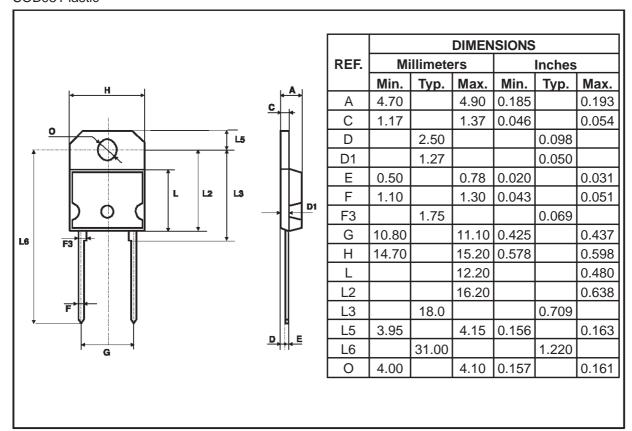
Figure 12. Turn-off switching characteristics (with series inductance)



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PACKAGE MECHANICAL DATA

SOD93 Plastic



Cooling method: by conduction (method C) Marking: type number Weight: 4.3g Recommended torque value: 80cm. N Maximum torque value: 100cm. N

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